

## **PATENT APPLICATION**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Mitsutoshi MIYASAKA

**Rule 53(b) Divisional of  
Application No.: 09/400,303**

Filed: March 19, 2002

Docket No.: 038839.02

For: A METHOD FOR FORMING CRYSTALLINE SEMICONDUCTOR LAYERS, A  
METHOD FOR FABRICATING THIN FILM TRANSISTORS, AND A METHOD FOR  
FABRICATING SOLAR CELLS AND ACTIVE MATRIX LIQUID CRYSTAL  
DEVICES

## PRELIMINARY AMENDMENT

Assistant Commissioner of Patents  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

**IN THE SPECIFICATION:**

**Page 1, line 1, delete in its entirety.**

Page 1, between lines 5 and 6, insert the following centered heading:

## BACKGROUND OF THE INVENTION

Page 1, line 6:

## Field of The Invention

Page 1, line 12:

### Description of the Related Art

Page 3, line 25:

## SUMMARY OF THE INVENTION